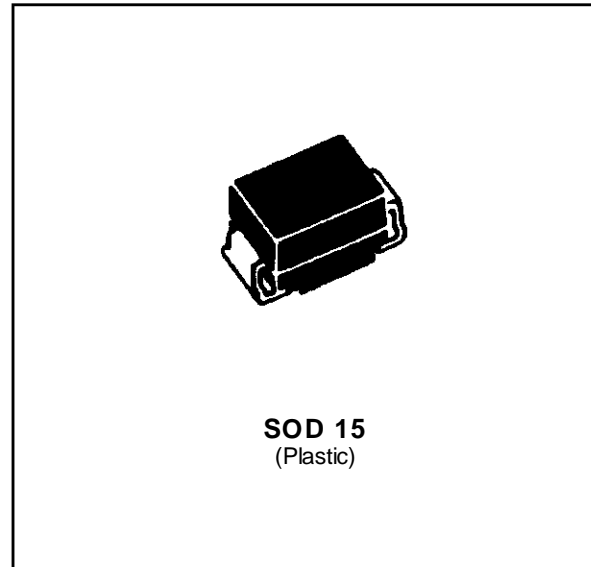


**TRISIL FOR SLIC PROTECTION**

**FEATURES**

- CROWBAR PROTECTION.
- ASYMETRICAL TRANSIENT SUPPRESSOR
- PEAK PULSE CURRENT :  
-  $I_{PP} = 75 \text{ A}$ ,  $10/1000 \mu\text{s}$ .
- HOLDING CURRENT =  $150 \text{ mA min}$
- BREAKDOWN VOLTAGE =  $58 \text{ V}$ .
- BREAKOVER VOLTAGE =  $80\text{V max}$ .

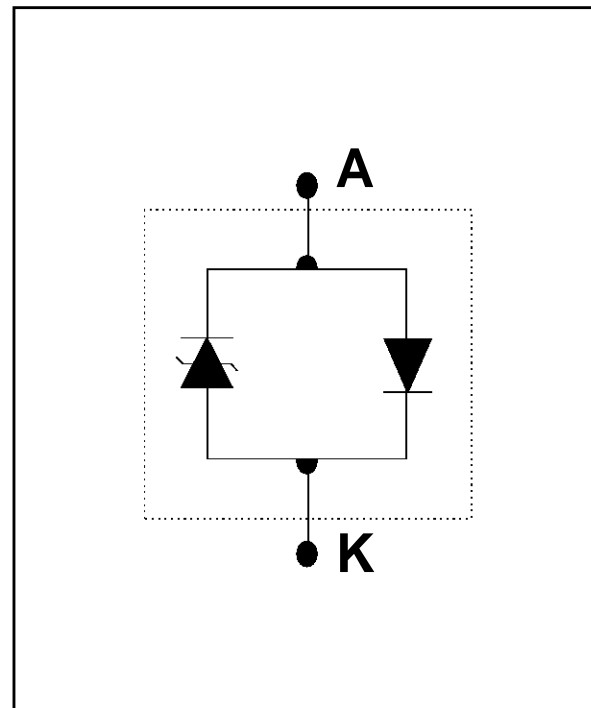


**DESCRIPTION**

This device has been especially designed to protect subscriber line card interfaces (SLIC) and terminals against transient overvoltages.

A diode clips positive overloads and a crowbar device protects against negative surges.

**SCHEMATIC DIAGRAM**



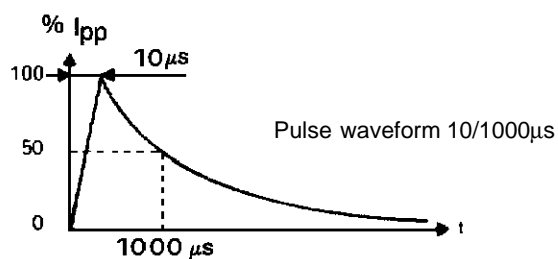
**IN ACCORDANCE WITH FOLLOWING STANDARDS :**

CCITT K17 - K20	{	10/700 $\mu\text{s}$	1.5 kV
		5/310 $\mu\text{s}$	38 A
VDE 0433	{	10/700 $\mu\text{s}$	2 kV
		5/200 $\mu\text{s}$	50 A
CNET	{	0.5/700 $\mu\text{s}$	1.5 kV
		0.2/310 $\mu\text{s}$	38 A

## SMTHDT58

### ABSOLUTE RATINGS (limiting values) ( $-40^{\circ}\text{C} \leq T_{\text{amb}} \leq +85^{\circ}\text{C}$ )

Symbol	Parameter	Value	Unit
$I_{\text{PP}}$	Peak pulse current	10/1000 $\mu\text{s}$ 8/20 $\mu\text{s}$	A
$I_{\text{TSM}}$	Non repetitive surge peak on-state current	$t_p = 20 \text{ ms}$	A
$I_{\text{FSM}}$	Non repetitive surge peak forward current	$t_p = 20 \text{ ms}$	A
$di/dt$	Critical rate of rise of on-state current	Non repetitive	A/ $\mu\text{s}$
$dv/dt$	Critical rate of rise of off-state voltage	67% $V_{\text{BR}}$	KV/ $\mu\text{s}$
$T_{\text{stg}}$ $T_{\text{j}}$	Storage and operating junction temperature range	- 40 to + 150 150	$^{\circ}\text{C}$ $^{\circ}\text{C}$
$T_{\text{L}}$	Maximum lead temperature for soldering during 10 s.	260	$^{\circ}\text{C}$

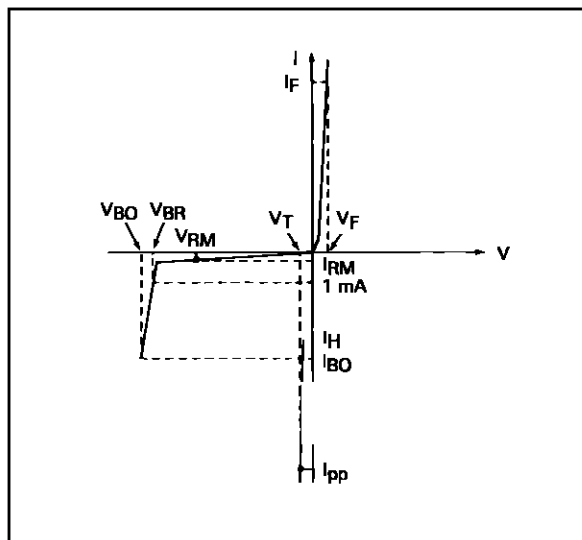


### THERMAL RESISTANCES

Symbol	Parameter	Value	Unit
$R_{\text{th}}(\text{j-l})$	Junction to leads	10	$^{\circ}\text{C}/\text{W}$
$R_{\text{th}}(\text{j-a})$	Junction-to-ambient	75	$^{\circ}\text{C}/\text{W}$

**ELECTRICAL CHARACTERISTICS**

Symbol	Parameter
$V_{RM}$	Stand-off voltage
$V_{BR}$	Breakdown voltage
$V_{BO}$	Breakover voltage
$I_H$	Holding current
$V_T$	On-state voltage
$V_F$	Forward Voltage Drop
$I_{BO}$	Breakover current
$I_{PP}$	Peak pulse current



**PARAMETER RELATED TO THE DIODE.**

Symbol	Test conditions	Value	Unit
$V_F$	Square pulse, $t_p = 500 \mu s$ , $I_F = 5 A$ .	5	V

**PARAMETERS RELATED TO THE PROTECTION THYRISTOR.**

TYPE	$I_{RM}$ @ $V_{RM}$		$V_{BR}$ @ $I_R$		$V_{BO}$ @ $I_{BO}$			$I_H$	$V_T$	C
	max		min		max	min	max	min	max	max
	$\mu A$	V	V	mA	V	mA	mA	mA	V	pF
SMTHDT58	10	56	58	1	80	150	800	150	5	400

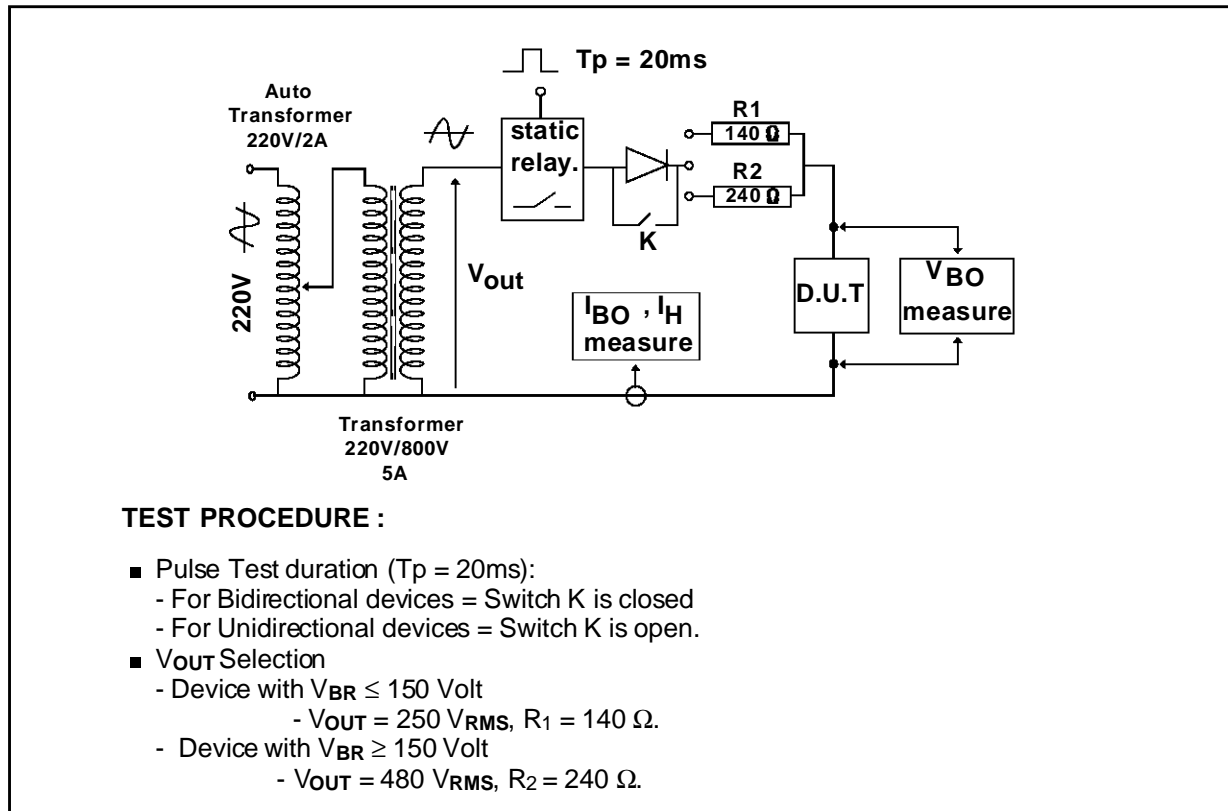
All parameters tested at 25°C, except where indicated

**Note 1 :** See the reference test circuit for  $I_H$ ,  $I_{BO}$  and  $V_{BO}$  parameters.

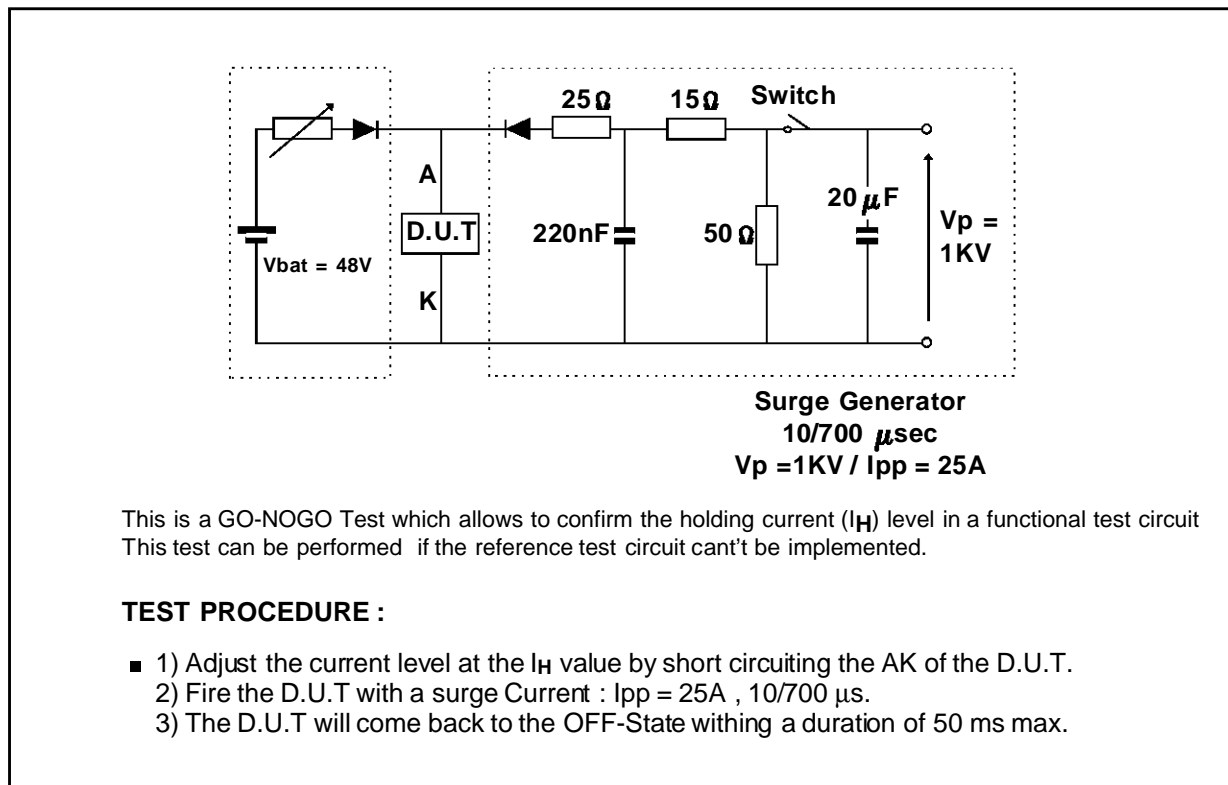
**Note 2 :** Square pulse  $T_p = 500 \mu s$  -  $I_T = 5 A$ .

**Note 3 :**  $V_R = 1 V$ ,  $F = 1 MHz$ .

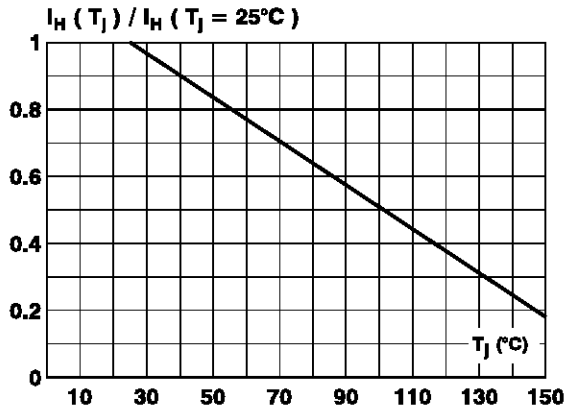
**REFERENCE TEST CIRCUIT FOR  $I_H$ ,  $I_{BO}$  and  $V_{BO}$  parameters :**



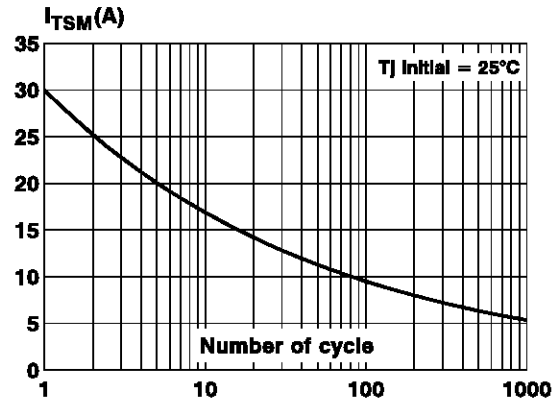
**FUNCTIONAL HOLDING CURRENT ( $I_H$ ) TEST CIRCUIT = GO - NOGO TEST.**



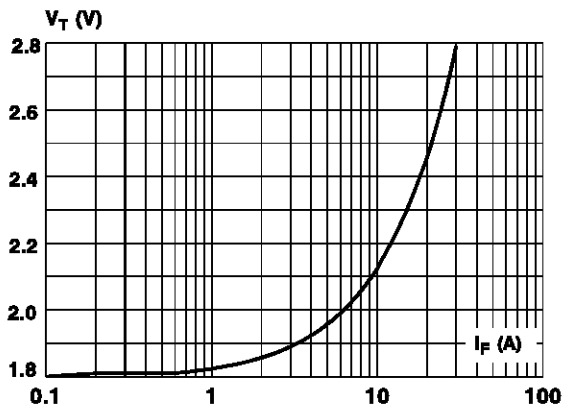
**Figure 1 :** Relative variation of holding current versus junction temperature.



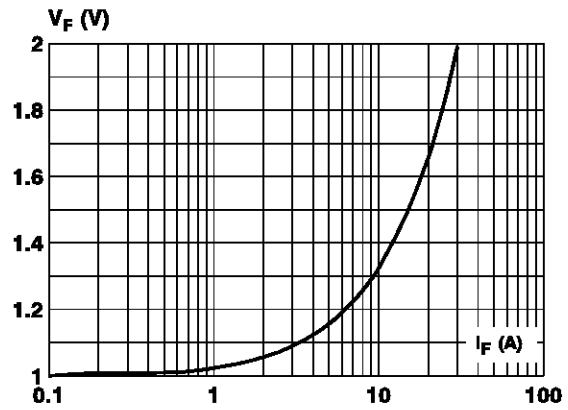
**Figure 2 :** Non repetitive surge peak on state current versus number of cycles (1 cycle = 20



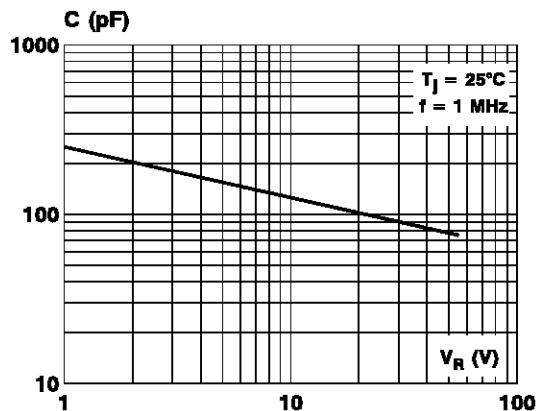
**Figure 3 :** Peak on state voltage versus peak on state current (typical values).



**Figure 4 :** Peak forward voltage drop versus peak forward current (typical values).



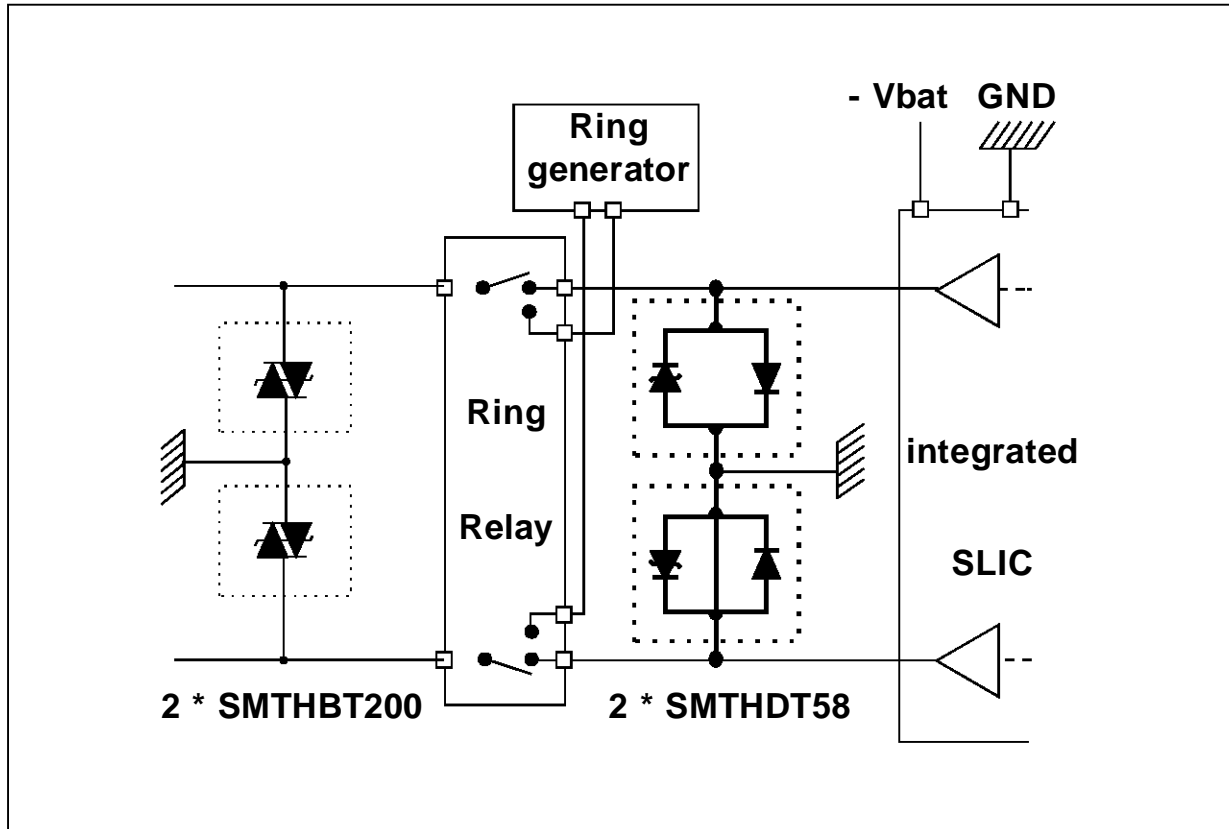
**Figure 5 :** Capacitance versus reverse applied voltage (typical values).



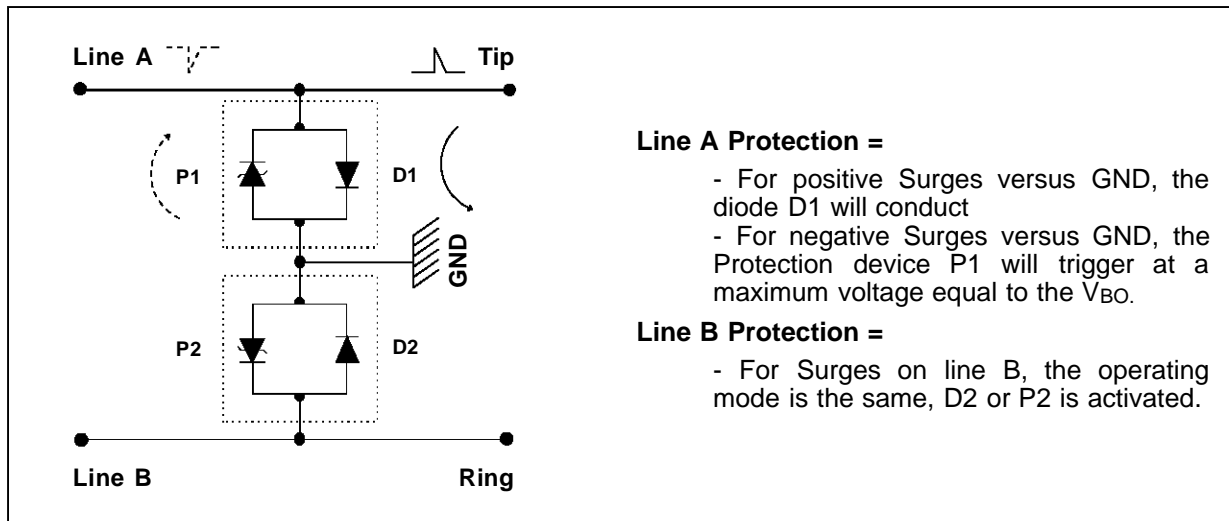
# SMTHDT58

## APPLICATION CIRCUIT

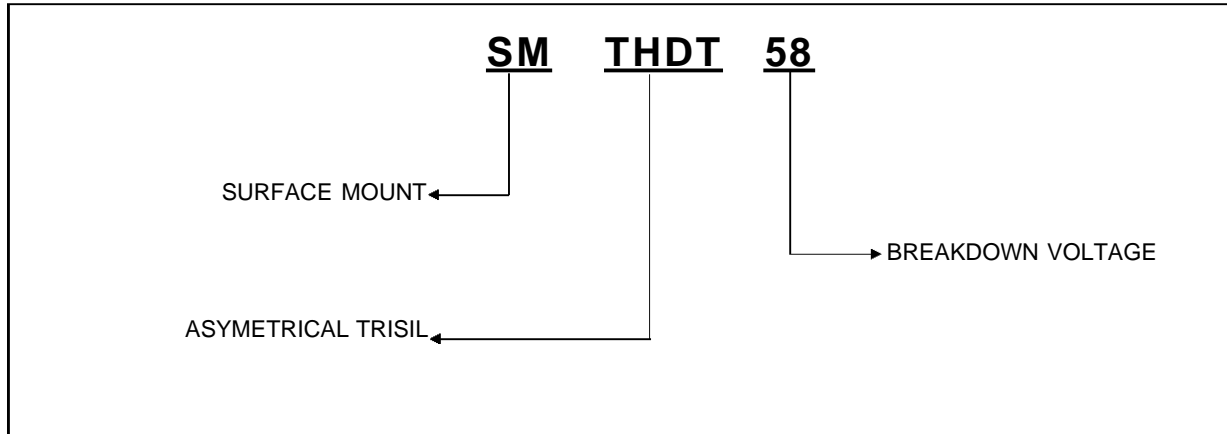
Typical slic protection concept



## FUNCTIONAL DESCRIPTION



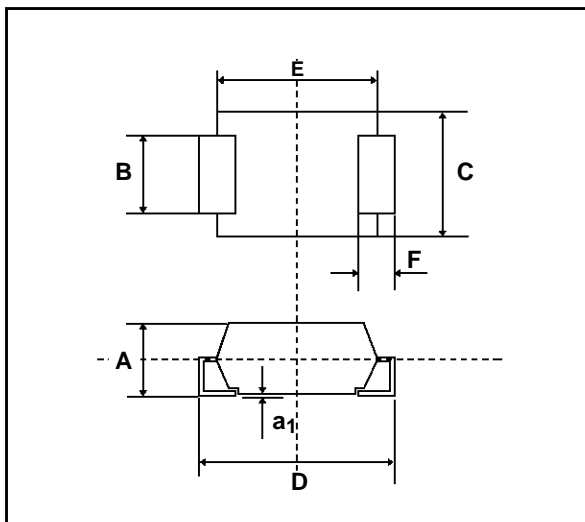
ORDER CODE



**MARKING =** Logo, WO1  
 A white band indicates the cathode.

**PACKAGE MECHANICAL DATA .**

SOD 15 Plastic.



Ref	Millimeters		Inches	
	min	max	min	max
A	2.5	3.1	0.098	0.122
a <sub>1</sub>	-	0.2	-	0.008
B	2.9	3.1	0.114	0.122
C	4.8	5.2	0.190	0.200
D	7.6	8.0	0.300	0.315
E	6.3	6.6	0.248	0.259
F	1.3	1.7	0.051	0.067

**Packaging :** Standard packaging is in film.

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